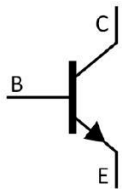


Silicon NPN transistor in a TO-126(R) Plastic Package.

High voltage.

High voltage switching and .

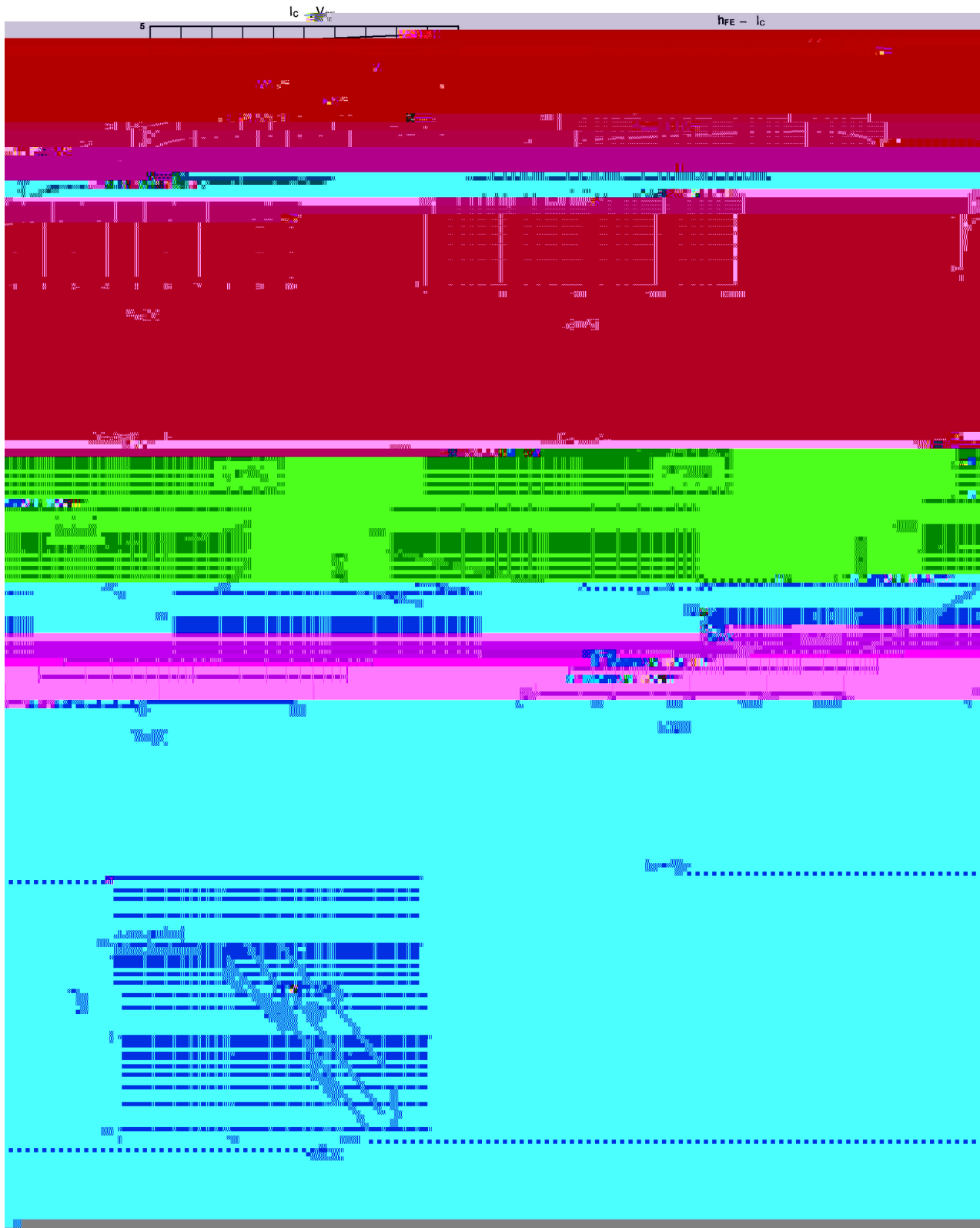


PIN1	Base	PIN 2	Collector	PIN 3	Emitter
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See Marking Instructions.

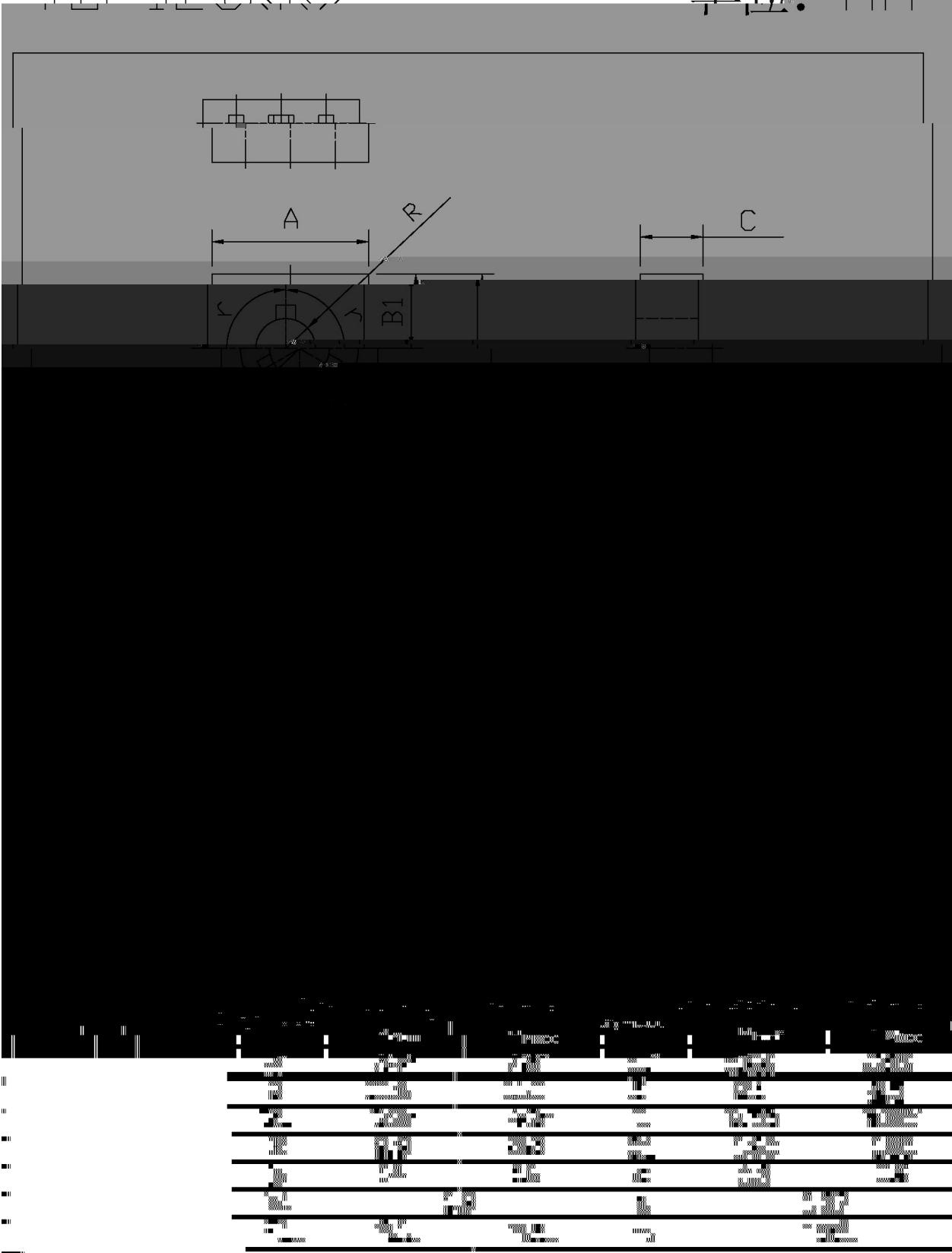
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	200	V
Collector to Emitter Voltage	V_{CEO}	120	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	7.0	A
Peak Collector Current	I_{Cp}	10	A
Base Current	I_B	2.0	A
Collector Power Dissipation	P_C	1.5	W
Collector Power Dissipation	$P_C(T_C=25^\circ\text{C})$	20	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55~150	

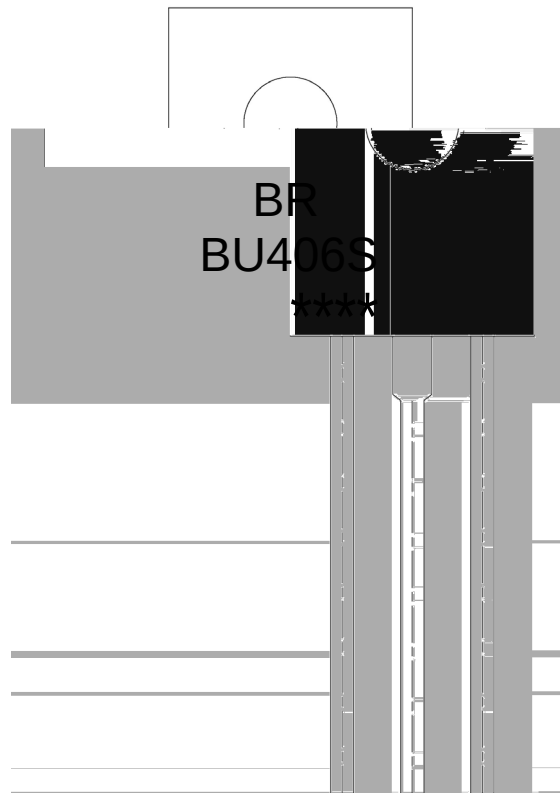
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	$I_{CES(1)}$	$V_{CE}=200V$ $V_{BE}=0$			100	μA
	$I_{CES(2)}$	$V_{CE}=150V$ $V_{BE}=0$			50	μA
	$I_{CES(3)}$	$V_{CE}=150V$ $V_{BE}=0$ T				



TT-126(R)

单位: mm





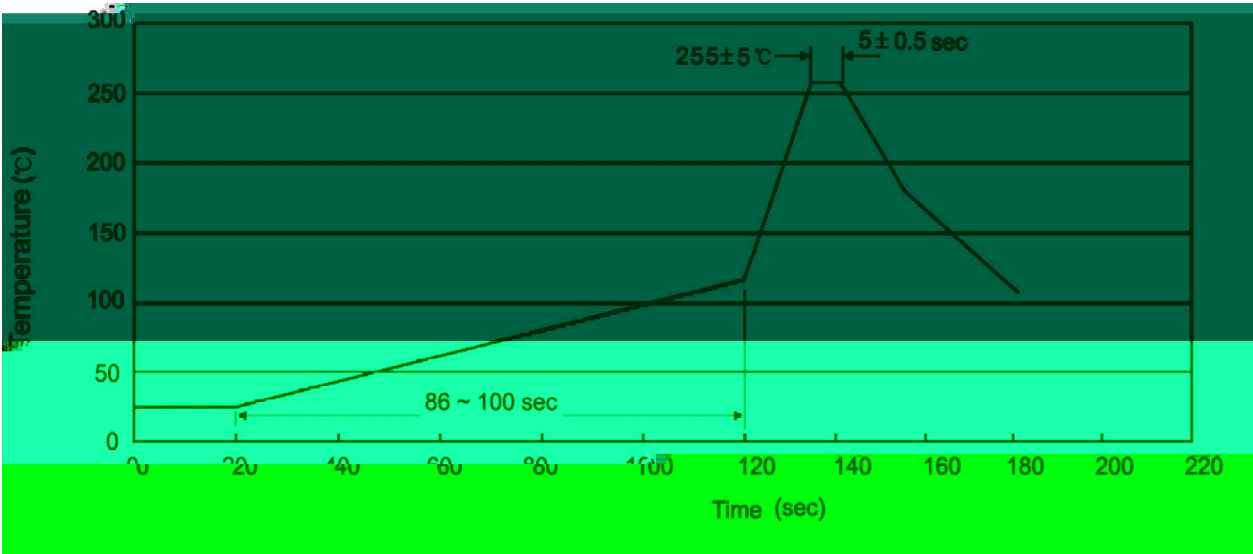
BR

Note:

BR: Company Code

BU406S: Product Type.

****: Lot No. Code, code change with Lot No.



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

270 5

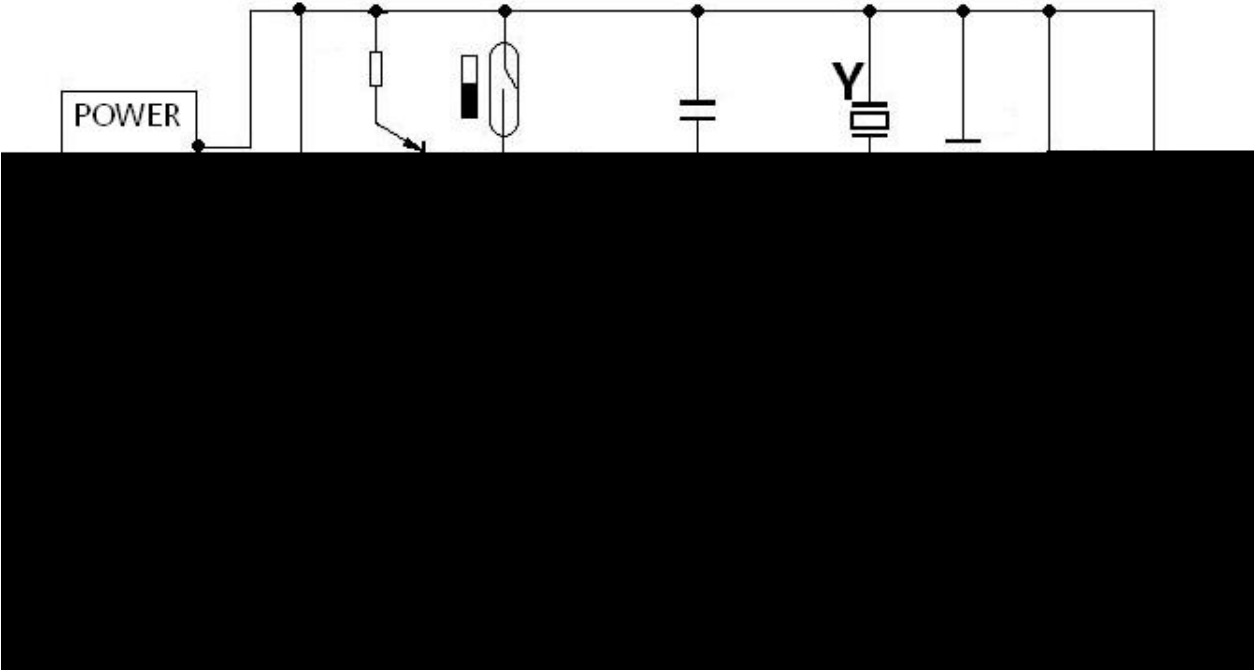
10 1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-126/F	500	6	3,000	5	15,000	135×190	237×172×102	560×245×195



Y